

## CLAIMS

1. An organic thin film transistor utilizing an organic semiconductor film, comprising a first substrate, a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, a drain electrode, a protective film and a second substrate.

2. An organic thin film transistor according to claim 1, wherein said protective film comprises a pliable substance.

3. An organic thin film transistor according to claim 1, wherein at least a part of said protective film comprises a pliable substance having a consistency within a range from 200 to 700.

4. An organic thin film transistor according to claim 1, wherein said protective film comprises a pliable substance and an insulation film.

5. An organic thin film transistor according to claim 1, wherein said protective film comprises a pliable substance and a light-shielding film.

6. An organic thin film transistor according to claim 1, wherein said protective film is formed from

a mixture containing a pliable substance and a hygroscopic material.

7. An organic thin film transistor according to claim 1, wherein said pliable substance is a vacuum grease.

8. An organic thin film transistor according to claim 1, wherein said hygroscopic material comprises calcium carbonate.

9. A method for producing an organic thin film transistor comprising a first substrate, a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, a drain electrode, a protective film and a second substrate, the method comprising:

forming a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, and a drain electrode on a first substrate, forming a protective film on a second substrate, and

superposing a surface, bearing the organic semiconductor film, of the first substrate upon a surface, bearing the protective film, of the second substrate.

10. A method for producing an organic thin film transistor according to claim 9, wherein said protective film comprises a pliable substance.

5 11. A method for producing an organic thin film transistor according to claim 9, wherein at least a part of said protective film comprises a pliable substance having a consistency within a range from 200 to 700.

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12. A method for producing an organic thin film transistor according to claim 9, wherein at least one of said source electrode and said drain electrode is formed by printing technology.

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13. An apparatus for producing an organic thin film transistor utilizing an organic semiconductor film, which superposes a protective film by a producing method according to claim 9, wherein a step  
20 of forming the organic semiconductor film and a step of superposing the protective film are successively carried out in the same apparatus.